# **Low Noise Transistors**

# **NPN Silicon**

## **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5088L MMBT5089L	V <sub>CEO</sub>	30 25	Vdc
Collector-Base Voltage MMBT5088L MMBT5089L	V <sub>CBO</sub>	35 30	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	4.5	Vdc
Collector Current – Continuous	I <sub>C</sub>	50	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

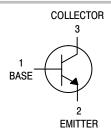


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SOT-23 (TO-236) CASE 318 STYLE 6



# **MARKING DIAGRAM**



1x = Device Code

x = Q for MMBT5088L SMMBT5088L x = R for MMBT5089L SMMBT5089L

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

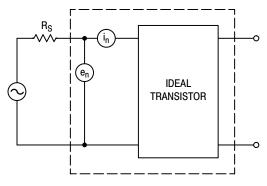
Device	Package	Shipping <sup>†</sup>
MMBT5088LT1G,	SOT-23	3,000 / Tape &
SMMBT5088LT1G	(Pb-Free)	Reel
NSVMMBT5088LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5089LT1G,	SOT-23	3,000 / Tape &
SMMBT5089LT1G	(Pb-Free)	Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	•
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	MMBT5088L MMBT5089L	V <sub>(BR)CEO</sub>	30 25	_ _	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	MMBT5088L MMBT5089L	V <sub>(BR)CBO</sub>	35 30	- -	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	MMBT5088L MMBT5089L	I <sub>CBO</sub>	- -	50 50	nAdc
Emitter Cutoff Current $(V_{EB(off)} = 3.0 \text{ Vdc}, I_C = 0)$ $(V_{EB(off)} = 4.5 \text{ Vdc}, I_C = 0)$	MMBT5088L MMBT5089L	I <sub>EBO</sub>	- -	50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc)	MMBT5088L MMBT5089L	h <sub>FE</sub>	300 400	900 1200	_
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		350 450	_ _	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		300 400	_ _	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)		V <sub>CE(sat)</sub>	-	0.5	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	-	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain — Bandwidth Product ( $I_C = 500 \mu Adc$ , $V_{CE} = 5.0 Vdc$ , $f = 20 MHz$ )		f <sub>T</sub>	50	_	MHz
Collector–Base Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz emitter guarded)		C <sub>cb</sub>	-	4.0	pF
Emitter-Base Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz collector guarded)		C <sub>eb</sub>	-	10	pF
Small Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	MMBT5088L MMBT5089L	h <sub>fe</sub>	350 450	1400 1800	-
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 10 k $\Omega$ , f = 1.0 kHz)	MMBT5088L MMBT5089L	NF	- -	3.0 2.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

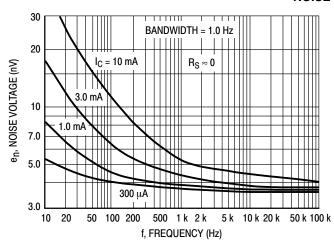


**Figure 1. Transistor Noise Model** 

## **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

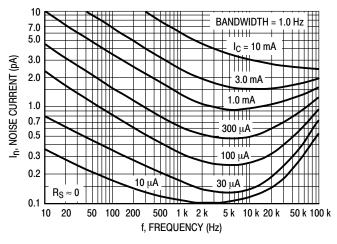
#### **NOISE VOLTAGE**



BANDWIDTH = 1.0 Hz 20  $R_S\approx 0\,$ en, NOISE VOLTAGE (nV) f = 10 Hz 10 100 Hz 7.0 5.0 3.0 0.02 0.01 0.05 0.1 0.2 0.5 1.0 2.0 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



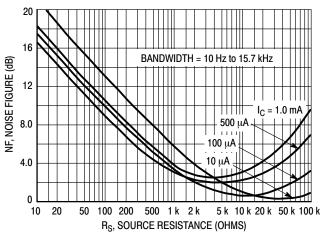
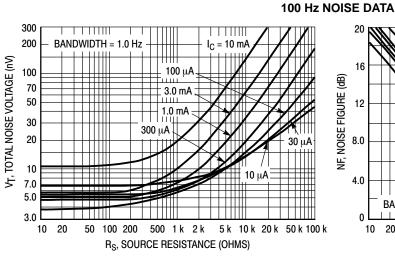
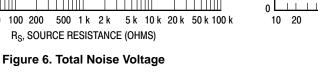


Figure 4. Noise Current

Figure 5. Wideband Noise Figure





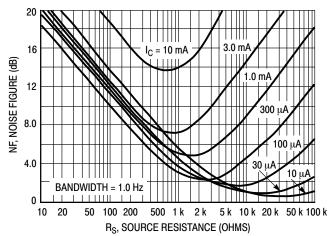


Figure 7. Noise Figure

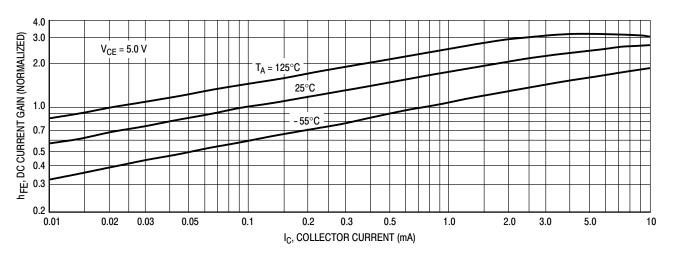


Figure 8. DC Current Gain

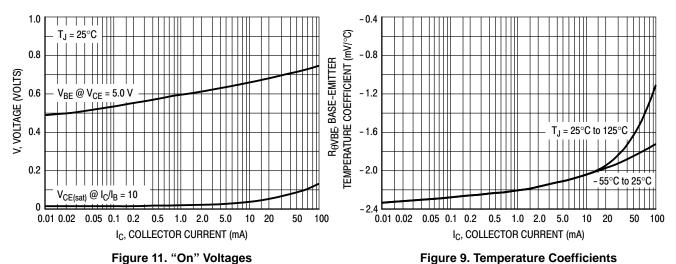


Figure 11. "On" Voltages

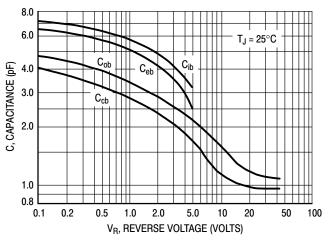


Figure 12. Capacitance

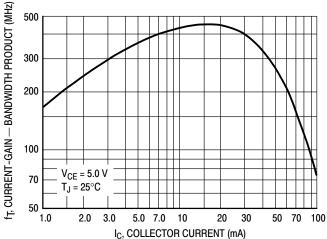


Figure 10. Current-Gain — Bandwidth Product



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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